EMB3 / UMB3N / IMB3A

PNP -100mA -50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Tr1 and Tr2
V_{CEO}	-50V
I _{C(MAX.)}	-100mA
R_1	4.7 k Ω

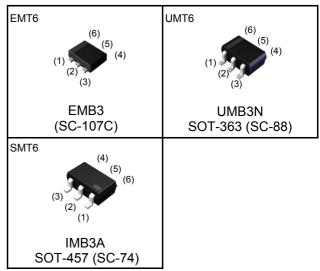
Features

- 1) Built-In Biasing Resistors.
- 2) Two DTA143T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

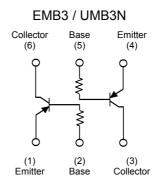
Application

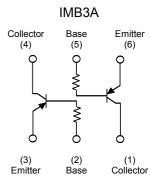
Inverter circuit, Interface circuit, Driver circuit

Outline



●Inner circuit





Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMB3	EMT6	1616	T2R	180	8	8,000	В3
UMB3N	UMT6	2021	TR	180	8	3,000	B3
IMB3A	SMT6	2928	T108	180	8	3,000	В3

● Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Paramete	Symbol	Values	Unit	
Collector-base voltage		V_{CBO}	-50	V
Collector-emitter voltage		V_{CEO}	-50	V
Emitter-base voltage		V_{EBO}	– 5	V
Collector current		I _{C(MAX.)} *1	-100	mA
Collector Power dissipation EMB3 / UMB3N		- P _D *2	150 (Total) ^{*3}	mW
IMB3A			300 (Total) ^{*4}	mW
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

●Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_CBO	$I_C = -50 \mu A$	-50	-	-	V
Collector-emitter breakdown voltage	BV_CEO	I _C = -1mA	-50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50 \mu A$	-5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -50V	-	-	-0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	ı	1	-0.5	μΑ
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C}$ / $I_{\rm B}$ = -5mA / -0.25mA	ı	ı	-0.3	V
DC current gain	h _{FE}	V_{CE} = -5V , I_{C} = -1mA ,	100	250	600	-
Input resistance	R ₁	-	3.29	4.7	6.11	kΩ
Transition frequency	f _T *1	$V_{CE} = -10V, I_{E} = 5mA,$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

^{*4 200}mW per element must not be exceeded.

●Electrical characteristic curves(Ta = 25°C)

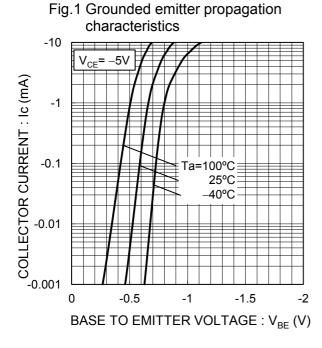
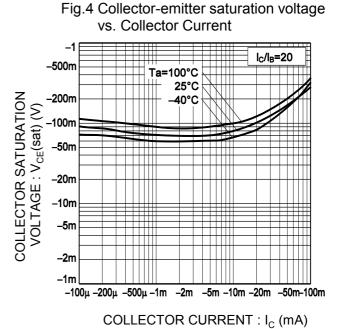
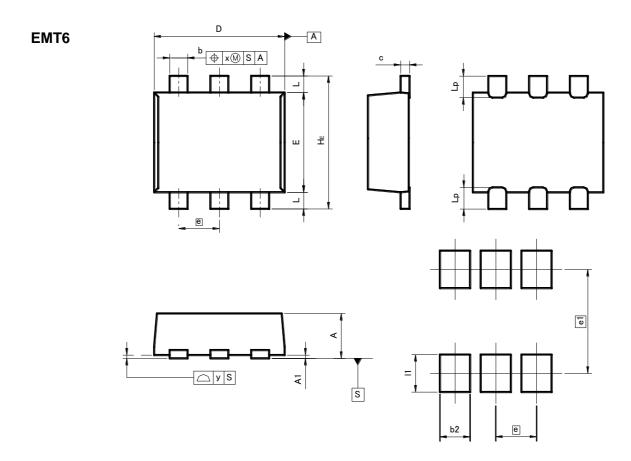


Fig.2 Grounded emitter output characteristics -100 $I_B =$ Ta=25°C 500µA 450µA COLLECTOR CURRENT : I_C (mA) -80 400µA -350µA 300µA -60 -250µA -200µA -40 -150µA -100µA -20 -50µA 0 0 -2 -6 -8 -10 **COLLECTOR TO EMITTER** VOLTAGE: V_{CF} (V)

Fig.3 DC Current gain vs. Collector Current V_{CE}= -5V 500 DC CURRENT GAIN: hFE 200 Ta=100°C 100 25°C 50 -40°C 20 10 5 -100μ -200μ -500μ -1m -2m -5m -10m -20m -50m -100mCOLLECTOR CURRENT : I_C (mA)



●Dimensions (Unit : mm)



Patterm of terminal position areas

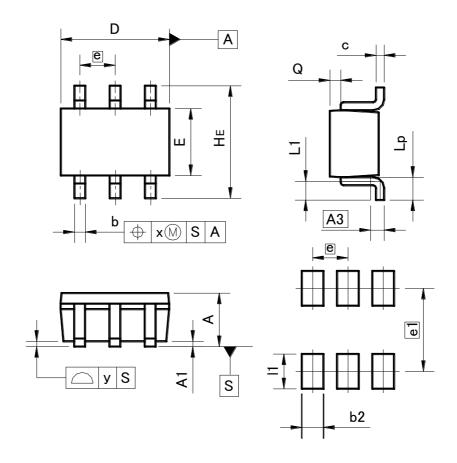
DIM	MILIMETERS		INC	HES
DIIVI	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
Α	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
е	0.	50	0.02	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	_	0.35	-	0.014
х	_	0.10	_	0.004
V	_	0.10	_	0.004

DIM -	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	_	0.37	ı	0.015	
11	_	0.45	ı	0.018	

Dimension in mm/inches

●Dimensions (Unit : mm)

UMT6



Patterm of terminal position areas

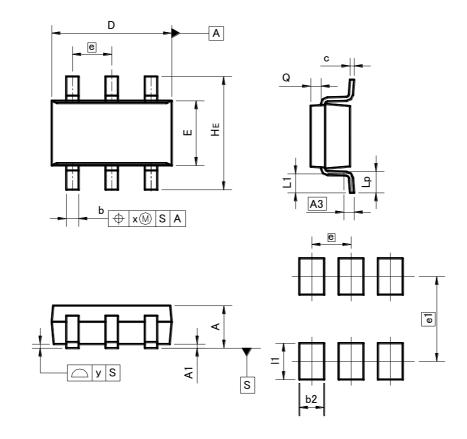
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	ı	0.039	
A1	0.00	0.10	0	0.004	
A3	0.2	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	-	0.10	_	0.004	
у	-	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX	
e1	1.55		0.06		
b2	_	0.40	-	0.016	
l1	_	0.65	1	0.026	

Dimension in mm/inches

●Dimensions (Unit : mm)

SMT6



Patterm of terminal position areas

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0	0.004
A3	0.2	25	0.0	01
b	0.25	0.40	0.01	0.016
С	0.09	0.25	0.004	0.01
D	2.80	3.00	0.11	0.118
E	1.50	1.80	0.059	0.071
е	0.0	95	0.04	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20	_	0.008
у	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	_	0.024	
11		0.90	-	0.035	

Dimension in mm/inches

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